

In the Claims:

1. (currently amended) A silicon single crystal wafer for a particle monitor, wherein said wafer is prepared by slicing a silicon single crystal ingot grown by the Czochralski method or slicing the silicon single crystal ingot and cleaning the wafer,

wherein said wafer has a wafer surface formed by said slicing of the silicon single crystal or by said slicing and cleaning, the wafer surface including [[includes]] an area in which crystal originated particles are generated,

wherein a surface density of particles having a particle size of not less than 0.12  $\mu\text{m}$  on the wafer surface is not more than 15 counts/cm<sup>2</sup>, even after repeating a Standard Cleaning -1, which is made using alkaline chemical liquid mainly containing NH<sub>4</sub>OH, H<sub>2</sub>O<sub>2</sub>, and H<sub>2</sub>O.

2. (original) A silicon single crystal wafer for a particle monitor according to Claim 1, wherein said wafer has an oxygen concentration of not more than  $13 \times 10^{17}$  atoms/cm<sup>3</sup> (old ASTM).

3. (currently amended) A silicon single crystal wafer for a particle monitor, wherein said wafer is prepared by slicing a silicon single crystal ingot grown by the Czochralski method,

wherein said wafer has a wafer surface formed by said slicing of the silicon single crystal or by said slicing and cleaning, the wafer surface including [[includes]] an area in which crystal originated particles are generated, and further said silicon single crystal ingot has a nitrogen concentration of  $1 \times 10^{13} - 1 \times 10^{15}$  atoms/cm<sup>3</sup>,

wherein a surface density of particles having a particle size of not less than 0.12  $\mu\text{m}$  on the wafer surface is not more than 1 count/ $\text{cm}^2$ , even after repeating a Standard Cleaning -1, which is made using alkaline chemical liquid mainly containing  $\text{NH}_4\text{OH}$ ,  $\text{H}_2\text{O}_2$ , and  $\text{H}_2\text{O}$ .

4. (original) A silicon single crystal wafer for a particle monitor according to Claim 3, wherein said wafer has an oxygen concentration of not more than  $13 \times 10^{17}$  atoms/ $\text{cm}^3$  (old ASTM).

5. (currently amended) A silicon single crystal wafer for a particle monitor, wherein said wafer is prepared by slicing a silicon single crystal ingot grown by the Czochralski method,

wherein said wafer has a wafer surface formed by said slicing of the silicon single crystal or by said slicing and cleaning, forming of the ingot ~~[[includes,]]~~ in said Czochralski method, including controlling a ~~[[the]]~~ time period of passing ~~[[the]]~~ a temperature range from 1150°C to 1070°C ~~[[is]]~~ to be within 20 min and controlling a ~~[[the]]~~ time period of passing ~~[[the]]~~ a temperature range from 900°C to 800°C ~~[[is]]~~ to be within 40 min,

wherein a surface density of particles having a particle size of not less than 0.12  $\mu\text{m}$  on the wafer surface is not more than 15 counts/ $\text{cm}^2$ , even after repeating a Standard Cleaning -1, which is made using alkaline chemical liquid mainly containing  $\text{NH}_4\text{OH}$ ,  $\text{H}_2\text{O}_2$ , and  $\text{H}_2\text{O}$ .

6. (original) A silicon single crystal wafer for a particle monitor according to Claim 5, wherein said wafer has an oxygen concentration of not more than  $13 \times 10^{17}$  atoms/cm<sup>3</sup> (old ASTM).

7. (currently amended) A silicon single crystal wafer for a particle monitor, wherein said wafer is prepared by slicing a silicon single crystal ingot grown by the Czochralski method,

wherein in said Czochralski method, a [[the]] time period of passing [[the]] a temperature range from 1150°C to 1070°C is within 20 min and a [[the]] time period of passing [[the]] a temperature range from 900°C to 800°C is within 40 min,

wherein said silicon single crystal ingot has a nitrogen concentration of  $1 \times 10^{13}$  –  $1 \times 10^{15}$  atoms/cm<sup>3</sup>,

wherein a surface density of particles having a particle size of not less than 0.12 μm on the wafer surface is not more than 1 count/cm<sup>2</sup>, even after repeating a Standard Cleaning -1, which is made using alkaline chemical liquid mainly containing NH<sub>4</sub>OH, H<sub>2</sub>O<sub>2</sub>, and H<sub>2</sub>O.

8. (original) A silicon single crystal wafer for a particle monitor according to Claim 7, wherein said wafer has an oxygen concentration of not more than  $13 \times 10^{17}$  atoms/cm<sup>3</sup> (old ASTM).

9. (previously presented) A silicon single crystal wafer for a particle monitor according to Claim 1, wherein, in said Standard Cleaning - 1, a chemical component of

a used solution is  $\text{H}_2\text{O}_2 : \text{NH}_4\text{OH} : \text{H}_2\text{O} = 1 : 1 : 5$ , the cleaning is repeated six times, and each cleaning is carried out for 10 min.

10. (previously presented) A silicon single crystal wafer for a particle monitor according to Claim 3, wherein, in said Standard Cleaning - 1, a chemical component of a used solution is  $\text{H}_2\text{O}_2 : \text{NH}_4\text{OH} : \text{H}_2\text{O} = 1 : 1 : 5$ , the cleaning is repeated six times, and each cleaning is carried out for 10 min.

11. (previously presented) A silicon single crystal wafer for a particle monitor according to Claim 5, wherein, in said Standard Cleaning - 1, a chemical component of a used solution is  $\text{H}_2\text{O}_2 : \text{NH}_4\text{OH} : \text{H}_2\text{O} = 1 : 1 : 5$ , the cleaning is repeated six times, and each cleaning is carried out for 10 min.

12. (previously presented) A silicon single crystal wafer for a particle monitor according to Claim 7, wherein, in said Standard Cleaning - 1, a chemical component of a used solution is  $\text{H}_2\text{O}_2 : \text{NH}_4\text{OH} : \text{H}_2\text{O} = 1 : 1 : 5$ , the cleaning is repeated six times, and each cleaning is carried out for 10 min.

13. (new) A silicon single crystal wafer for a particle monitor according to claim 5, wherein said wafer surface is either a sliced wafer surface formed as a result of said slicing of the silicon single crystal or a sliced and cleaned wafer surface formed as a result of said slicing of the silicon single crystal and cleaning thereof.

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14. (new) A silicon single crystal wafer for a particle monitor according to claim 7, wherein said wafer surface is either a sliced wafer surface formed as a result of said slicing of the silicon single crystal or a sliced and cleaned wafer surface formed as a result of said slicing of the silicon single crystal and cleaning thereof.